ABSTRACT

The present invention provide a ceramic substrate for semiconductor manufacture and/or inspection which is conducive to decrease in α-rays radiated, and change of thermal conductivity with passage of the time, and which is superior in the temperature controllability.

This invention is related to a ceramic substrate for apparatuses for use in semiconductor manufacture and/or inspection,

wherein the level of α-rays radiated from said ceramic substrate exceeds 0.25 $c/cm^2 \cdot hr$ and is not higher than 50 $c/cm^2 \cdot hr$.